

# HiPerFET™ Power MOSFETs Single Die MOSFET

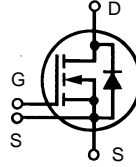
## IXFN 44N60

$$V_{DSS} = 600 \text{ V}$$

$$I_{D25} = 44 \text{ A}$$

$$R_{DS(on)} = 130 \text{ m}\Omega$$

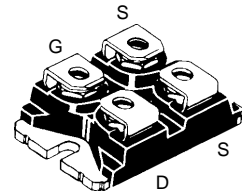
N-Channel Enhancement Mode  
Avalanche Rated, High dv/dt, Low  $t_{rr}$



$$t_{rr} \leq 250 \text{ ns}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	600	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	44	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	176	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	44	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	60	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	3	J
<b>dv/dt</b>	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	600	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_J$	1.6 mm (0.63 in) from case for 10 s	-	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	2500 3000	V~ V~
$M_d$	Mounting torque Terminal connection torque	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
<b>Weight</b>		30	g

miniBLOC, SOT-227 B  
E153432



G = Gate                      D = Drain  
S = Source                    TAB = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

### Features

- International standard package
- miniBLOC, with Aluminium nitride isolation
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

### Applications

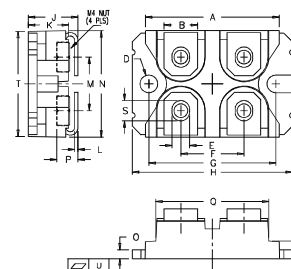
- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

### Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 3 \text{ mA}$	600		V
$V_{GH(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8 \text{ mA}$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$ , $T_J = 125^\circ\text{C}$			100 $\mu\text{A}$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2 \%$			130 m $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test	30	45	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		8900	pF
$C_{oss}$			1000	pF
$C_{rss}$			330	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		42	ns
$t_r$			55	ns
$t_{d(off)}$			110	ns
$t_f$			45	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		330	nC
$Q_{gs}$			60	nC
$Q_{gd}$			65	nC
$R_{thJC}$			0.21	K/W
$R_{thCK}$		0.05		K/W

**miniBLOC, SOT-227 B**


M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			44 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			176 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.3 V
$t_{rr}$	$I_F = 50\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
$Q_{RM}$			1.4	$\mu\text{C}$
$I_{RM}$			8	A

Figure 1. Output Characteristics at 25°C

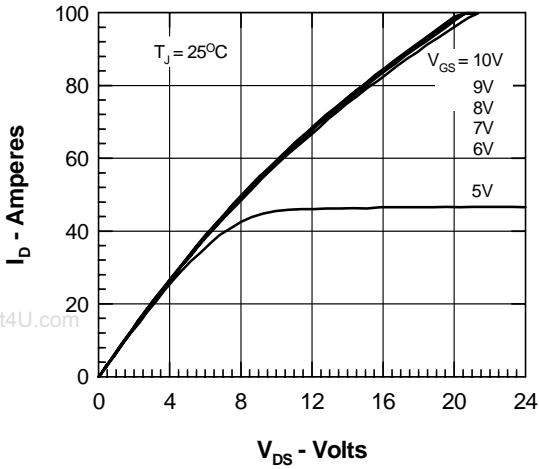


Figure 2. Output Characteristics at 125°C

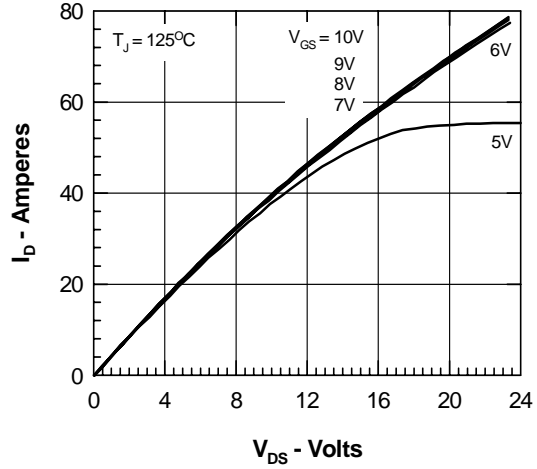


Figure 3.  $R_{DS(on)}$  normalized to 15A/25°C vs.  $I_D$

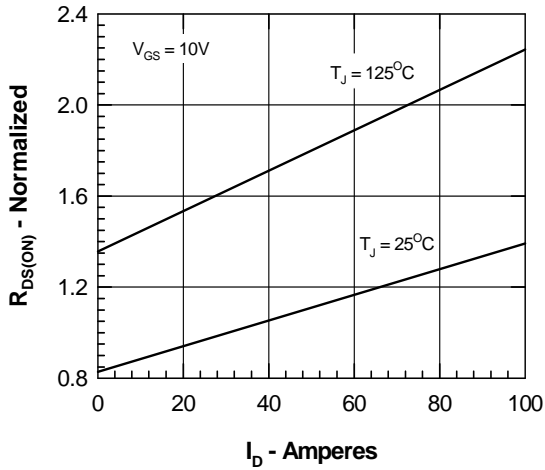


Figure 4.  $R_{DS(on)}$  normalized to 15A/25°C vs.  $T_J$

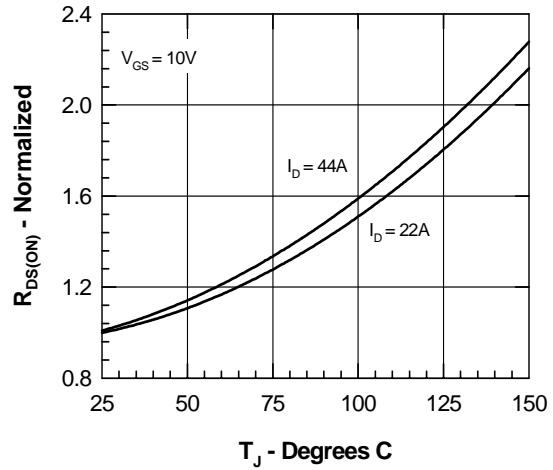


Figure 5. Drain Current vs. Case Temperature

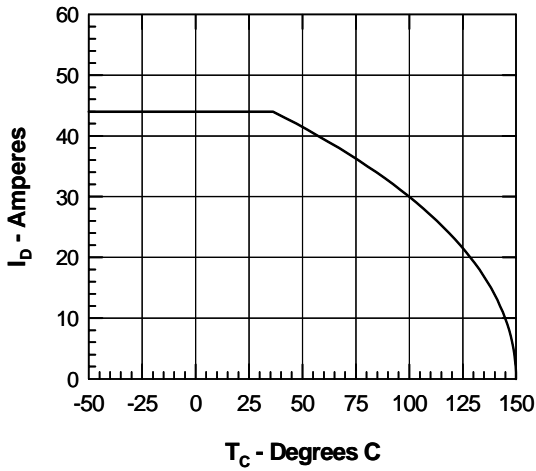


Figure 6. Admittance Curves

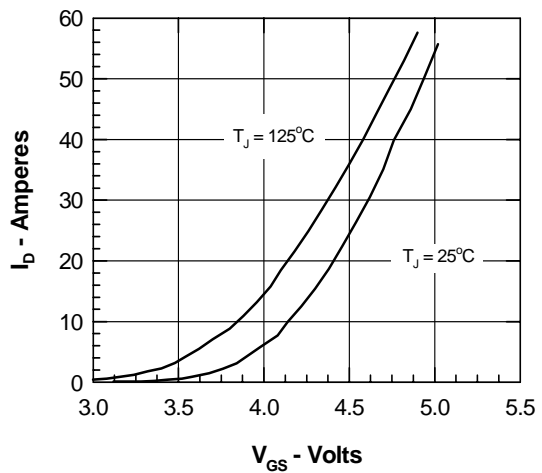


Figure 7. Gate Charge

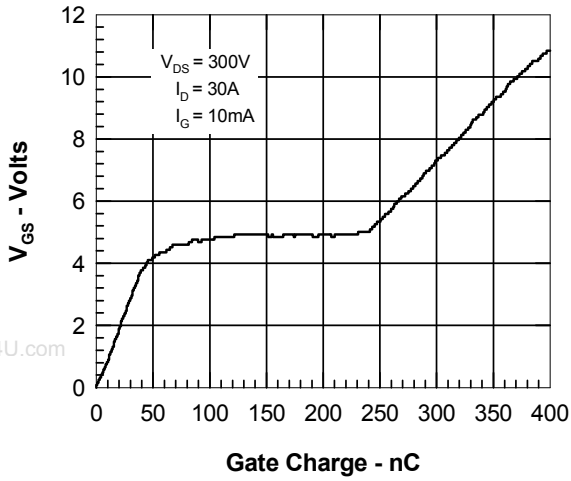


Figure 8. Capacitance Curves

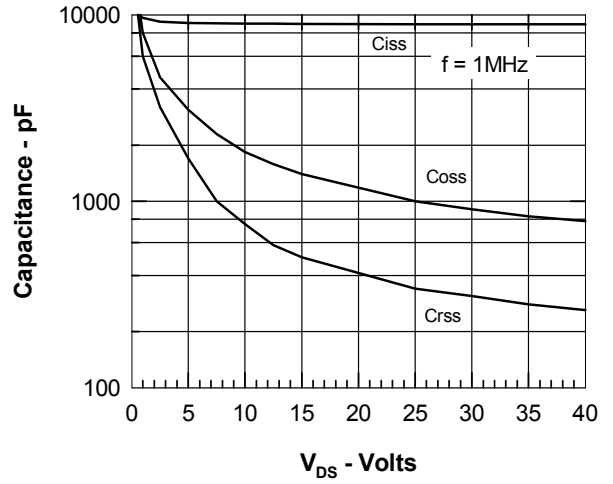


Figure 9. Forward Voltage Drop of the Intrinsic Diode

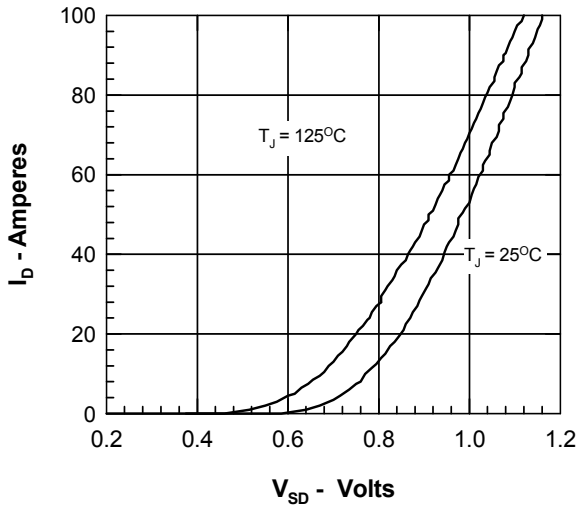


Figure 10. Transient Thermal Resistance

